

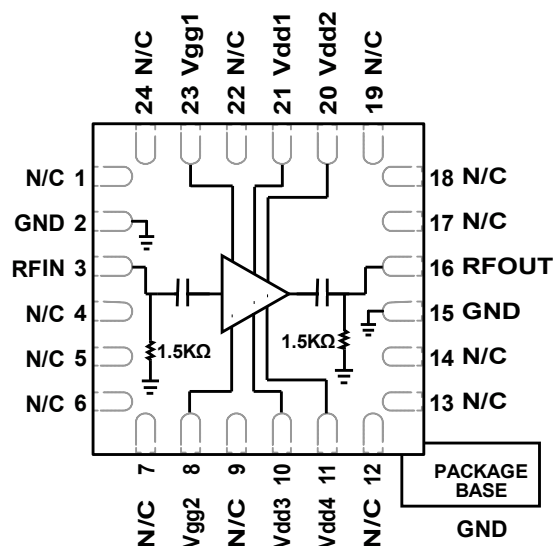
## GaAs pHEMT MMIC 2 WATT POWER AMPLIFIER, 5.5 - 8.5 GHz

### Typical Applications

The HMC7357LP5GE is ideal for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios
- VSAT & SATCOM

### Functional Diagram



### Features

- +35 dBm Pout @ 34% PAE
- High P1dB Output Power: +34 dBm
- High Output IP3: +41.5 dBm
- High Gain: 29 dB
- 50 Ohm Matched Input/Output
- Supply Voltage: Vdd = +8V @ 1200 mA
- 24-Lead 5x5 mm SMT Package

### General Description

The HMC7357LP5GE is a three-stage GaAs pHEMT MMIC Medium Power Amplifier that operates between 5.5 and 8.5 GHz. The amplifier provides 29 dB of gain and +35 dBm of saturated output power at 34% PAE from a +8V supply. With an excellent Output IP3 of +41.5 dBm, the HMC7357LP5GE is ideal for linear applications such as high capacity point-to-point and point-to-multi-point radios or VSAT/SATCOM applications demanding +35 dBm of efficient saturated output power. The RF I/Os are internally matched to 50 Ohms for ease of use. The HMC7357LP5GE is packaged in a leadless 5x5 mm plastic surface mount package and is compatible with surface mount manufacturing techniques.

### Electrical Specifications, $T_A = +25^\circ\text{C}$

Vdd = Vdd1 = Vdd2 = Vdd3 = Vdd4 = 8V, Idd = 1200 mA <sup>[1]</sup>

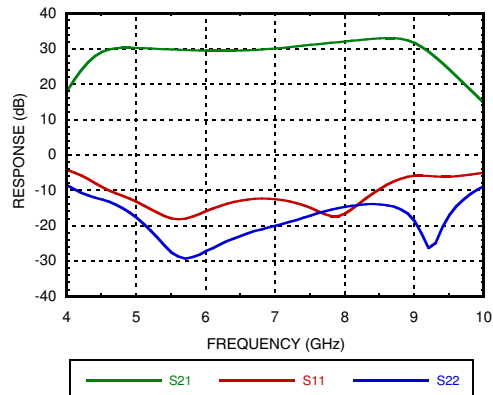
| Parameter                                         | Min.    | Typ.   | Max. | Min.    | Typ.   | Max. | Units |
|---------------------------------------------------|---------|--------|------|---------|--------|------|-------|
| Frequency Range                                   | 5.5 - 7 |        |      | 7 - 8.5 |        |      | GHz   |
| Gain                                              | 26.5    | 29.5   |      | 28      | 31     |      | dB    |
| Gain Variation Over Temperature                   |         | 0.0214 |      |         | 0.0234 |      | dB/°C |
| Input Return Loss                                 |         | 14     |      |         | 14     |      | dB    |
| Output Return Loss                                |         | 22     |      |         | 15     |      | dB    |
| Output Power for 1 dB Compression (P1dB)          | 31.5    | 34.5   |      | 31.5    | 34.5   |      | dBm   |
| Saturated Output Power (Psat)                     |         | 35     |      |         | 35     |      | dBm   |
| Output Third Order Intercept (IP3) <sup>[2]</sup> |         | 41.5   |      |         | 41.5   |      | dBm   |
| Total Supply Current (Idd)                        |         | 1200   |      |         | 1200   |      | mA    |

[1] Adjust Vgg between -2 to -0.4V to achieve Idd = 1200 mA typical.

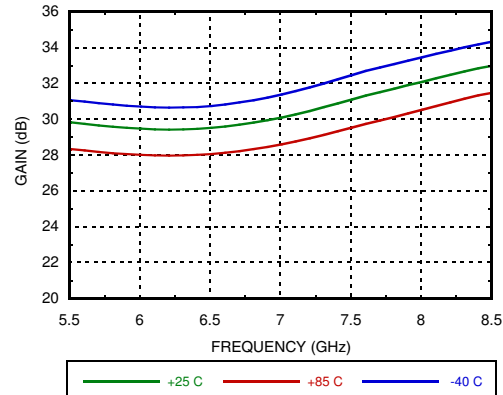
[2] Measurement taken at +8V @ 1200 mA, Pout / Tone = +20 dBm

**GaAs pHEMT MMIC 2 WATT  
POWER AMPLIFIER, 5.5 - 8.5 GHz**

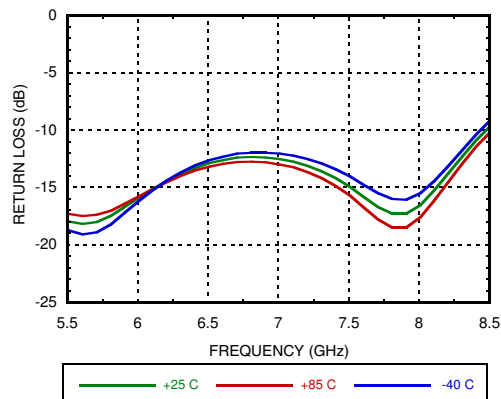
**Gain & Return Loss**



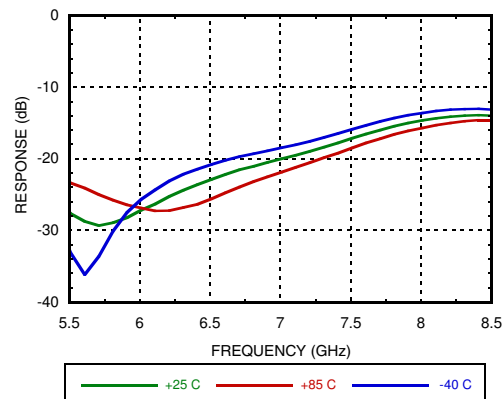
**Gain vs. Temperature**



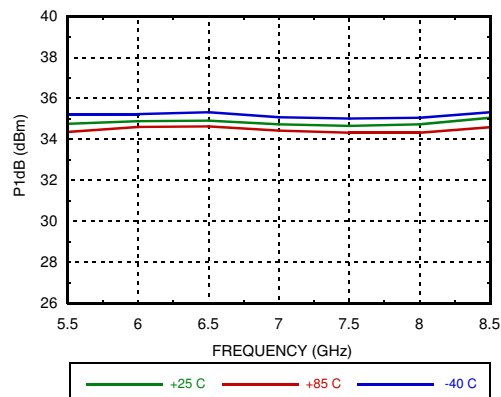
**Input Return Loss vs. Temperature**



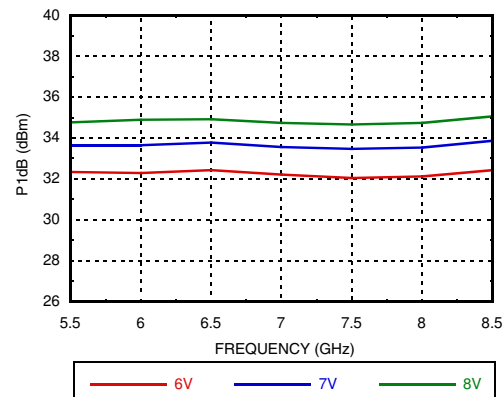
**Output Return Loss vs. Temperature**

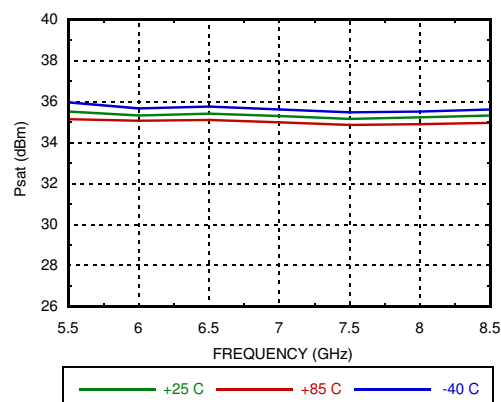
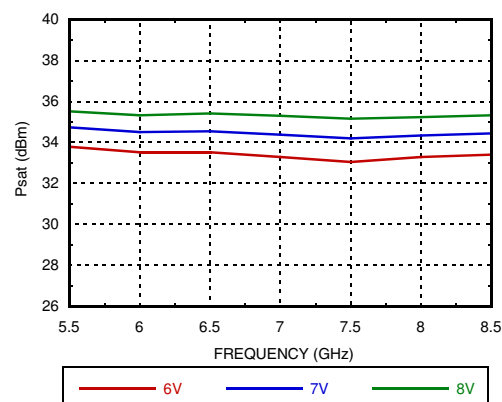
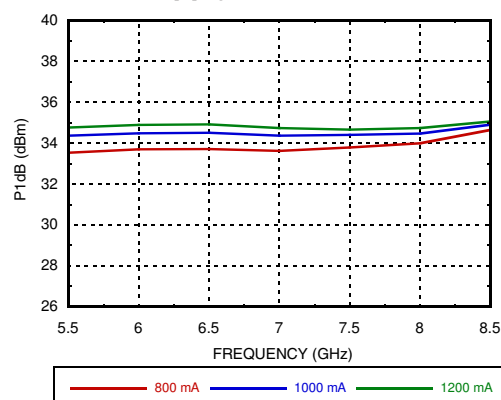
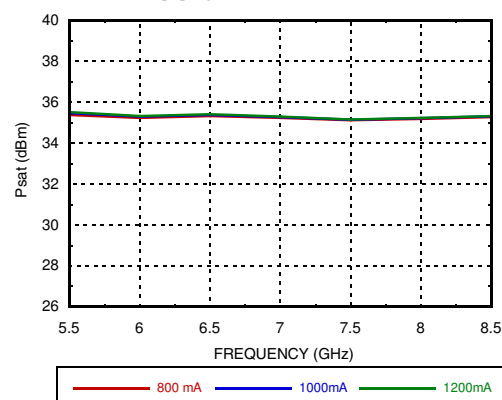
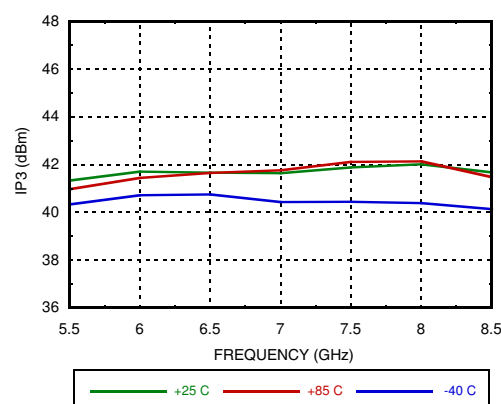
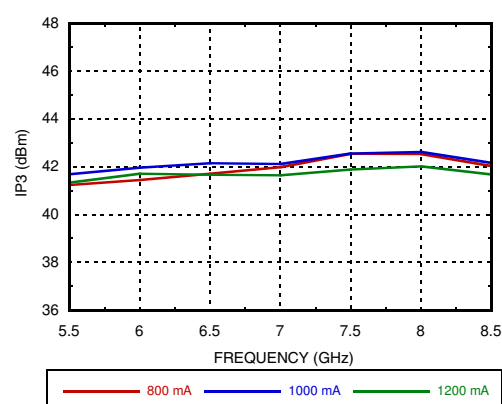


**P1dB vs. Temperature**



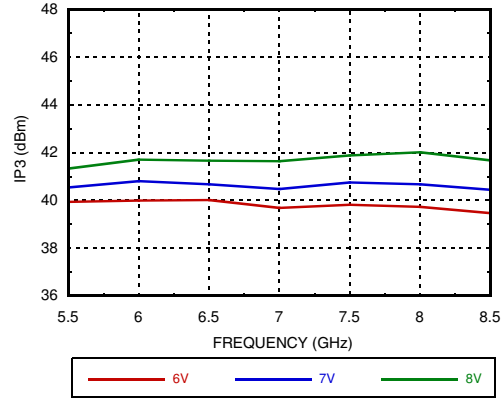
**P1dB vs. Supply Voltage**



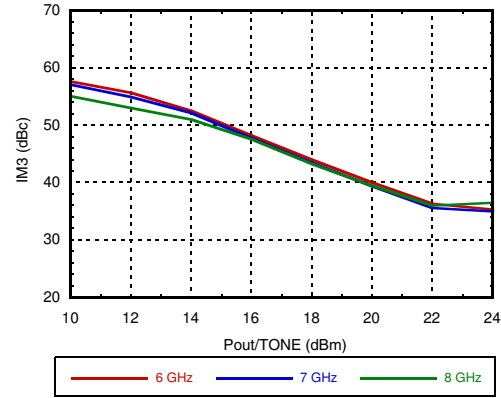
**GaAs pHEMT MMIC 2 WATT  
POWER AMPLIFIER, 5.5 - 8.5 GHz**
***Psat vs. Temperature***

***Psat vs. Supply Voltage***

***P1dB vs. Supply Current***

***Psat vs. Supply Current***

***Output IP3 vs. Temperature,  
Pout/tone = +20 dBm***

***Output IP3 vs. Supply Current,  
Pout/tone = +20 dBm***


## GaAs pHEMT MMIC 2 WATT POWER AMPLIFIER, 5.5 - 8.5 GHz

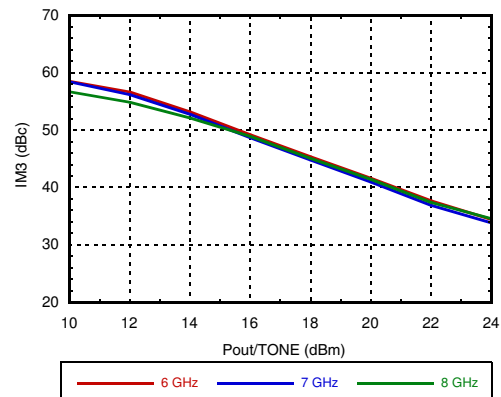
**Output IP3 vs. Supply Voltage,  
Pout/tone = +20 dBm**



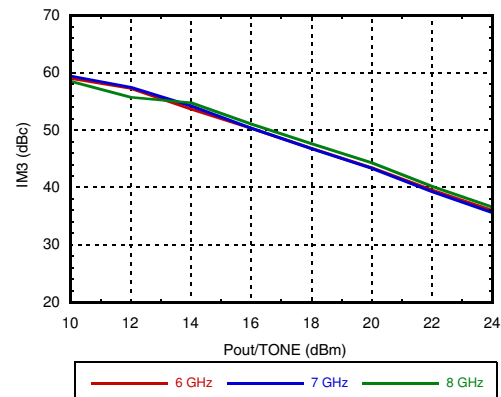
**Output IM3 @ Vdd = +6V**



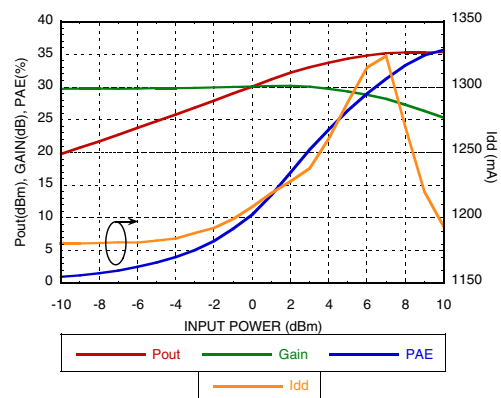
**Output IM3 @ Vdd = +7V**



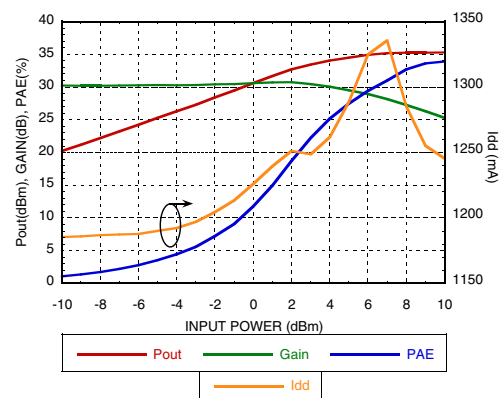
**Output IM3 @ Vdd = +8V**



**Power Compression @ 6 GHz**

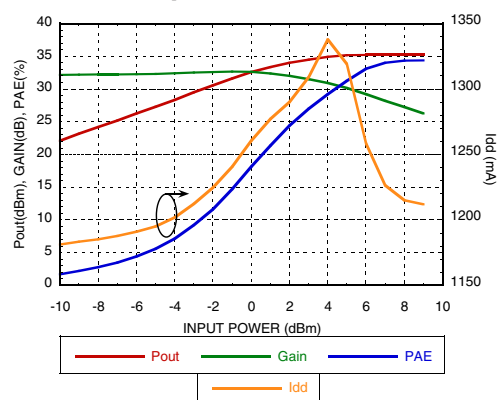


**Power Compression @ 7 GHz**

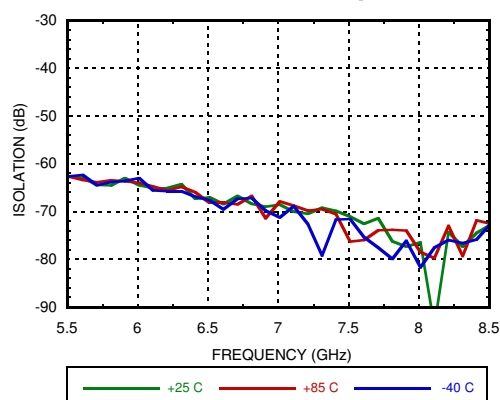


**GaAs pHEMT MMIC 2 WATT  
POWER AMPLIFIER, 5.5 - 8.5 GHz**

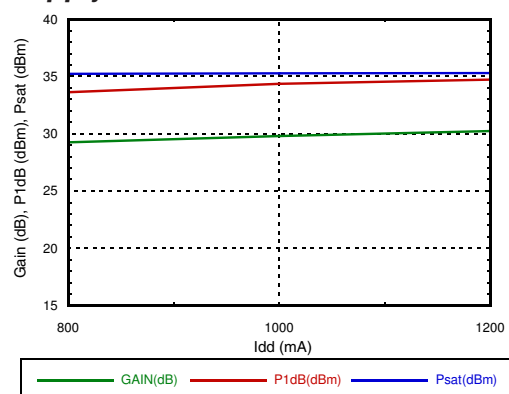
**Power Compression @ 8 GHz**



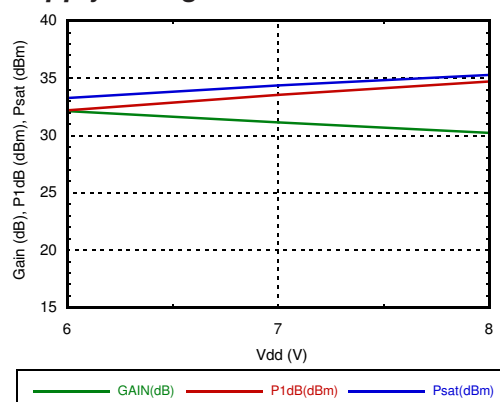
**Reverse Isolation vs. Temperature**



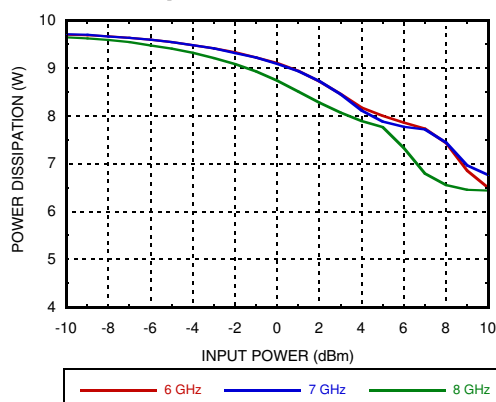
**Gain & Power vs.  
Supply Current @ 7 GHz**



**Gain & Power vs.  
Supply Voltage @ 7 GHz**



**Power Dissipation**



## GaAs pHEMT MMIC 2 WATT POWER AMPLIFIER, 5.5 - 8.5 GHz

### Absolute Maximum Ratings

|                                                              |                       |
|--------------------------------------------------------------|-----------------------|
| Drain Bias Voltage (Vdd)                                     | +9 Vdc                |
| Gate Bias Voltage (Vgg)                                      | -2 to -0.4 Vdc        |
| RF Input Power (RFIN)                                        | +22 dBm               |
| Channel Temperature                                          | 175 °C                |
| Continuous Pdiss (T= 85 °C)<br>(derate 135mW/°C above 85 °C) | 12.2 W                |
| Thermal Resistance<br>(channel to ground paddle)             | 7.38 °C/W             |
| Storage Temperature                                          | -65 to 150 °C         |
| Operating Temperature                                        | -40 to 85 °C          |
| ESD Sensitivity (HBM)                                        | Class 1A, passed 250V |

### Typical Supply Current vs. Vdd

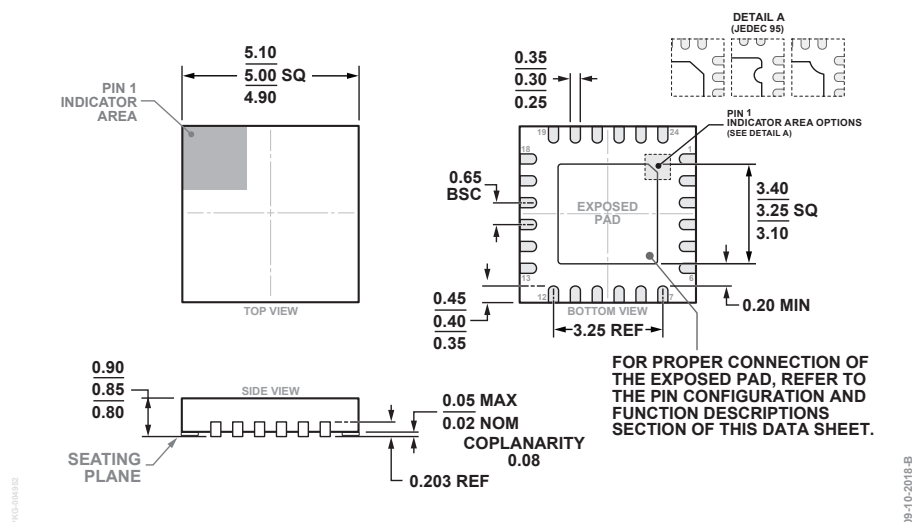
| Vdd (V) | Idd (mA) |
|---------|----------|
| +6      | 1200     |
| +7      | 1200     |
| +8      | 1200     |

Adjust Vgg to achieve Idd = 1200 mA



ELECTROSTATIC SENSITIVE DEVICE  
OBSERVE HANDLING PRECAUTIONS

### Outline Drawing



24-Lead Lead Frame Chip Scale Package [LFCSP]  
5 mm x 5 mm Body and 0.85 mm Package Height  
(CP-24-20)  
Dimensions shown in millimeters.

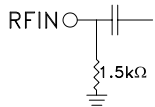
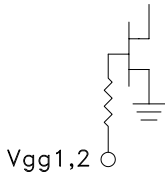
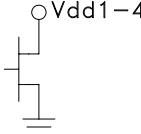
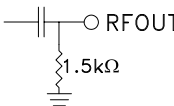
### Package Information

| Part Number  | Package Body Material                              | Lead Finish   | MSL Rating [2] | Package Marking [1] |
|--------------|----------------------------------------------------|---------------|----------------|---------------------|
| HMC7357LP5GE | RoHS-compliant Low Stress Injection Molded Plastic | 100% matte Sn | MSL3           | H7357<br>XXXX       |

[1] 4-Digit lot number XXXX

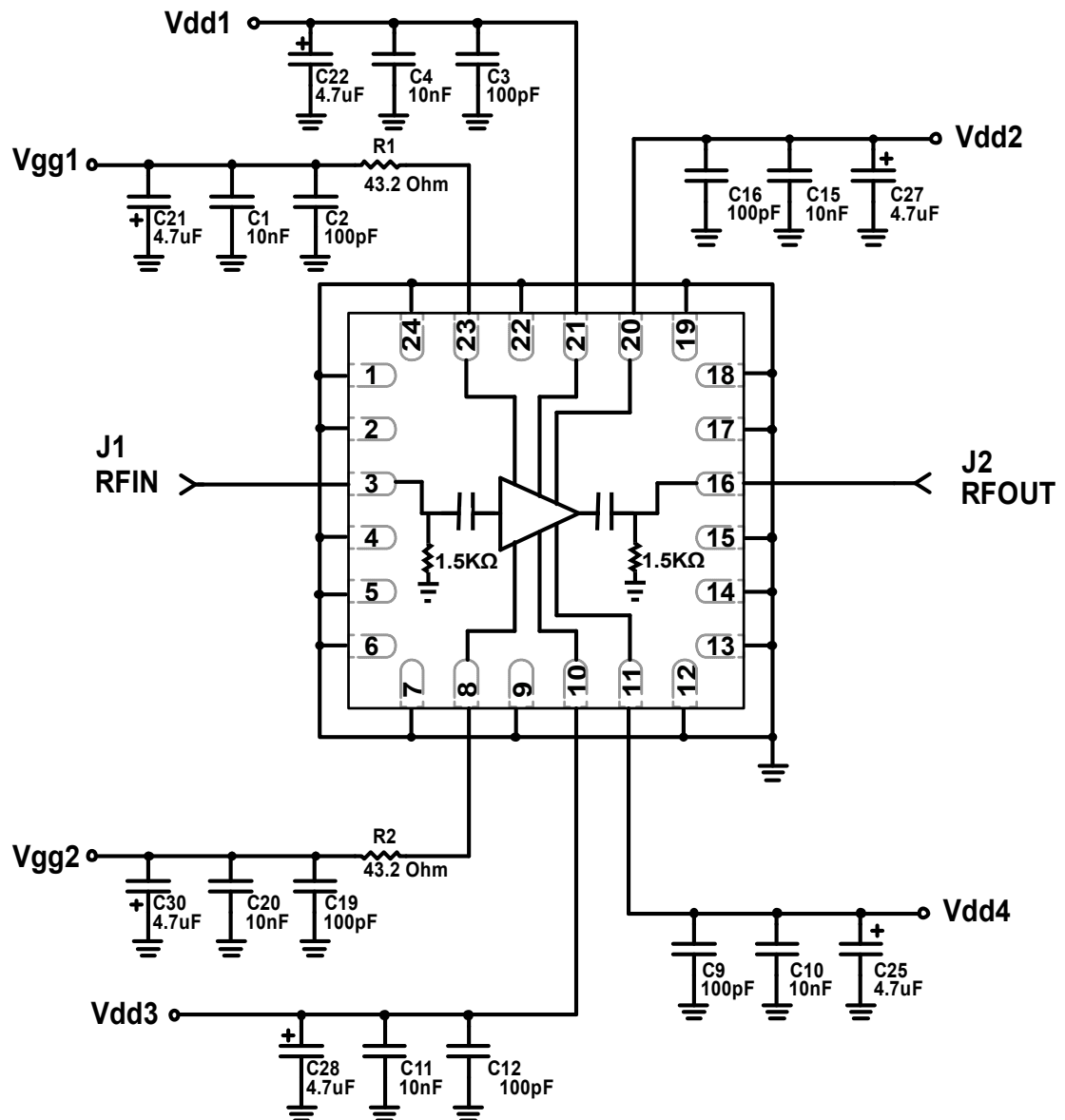
[2] Max peak reflow temperature of 260 °C

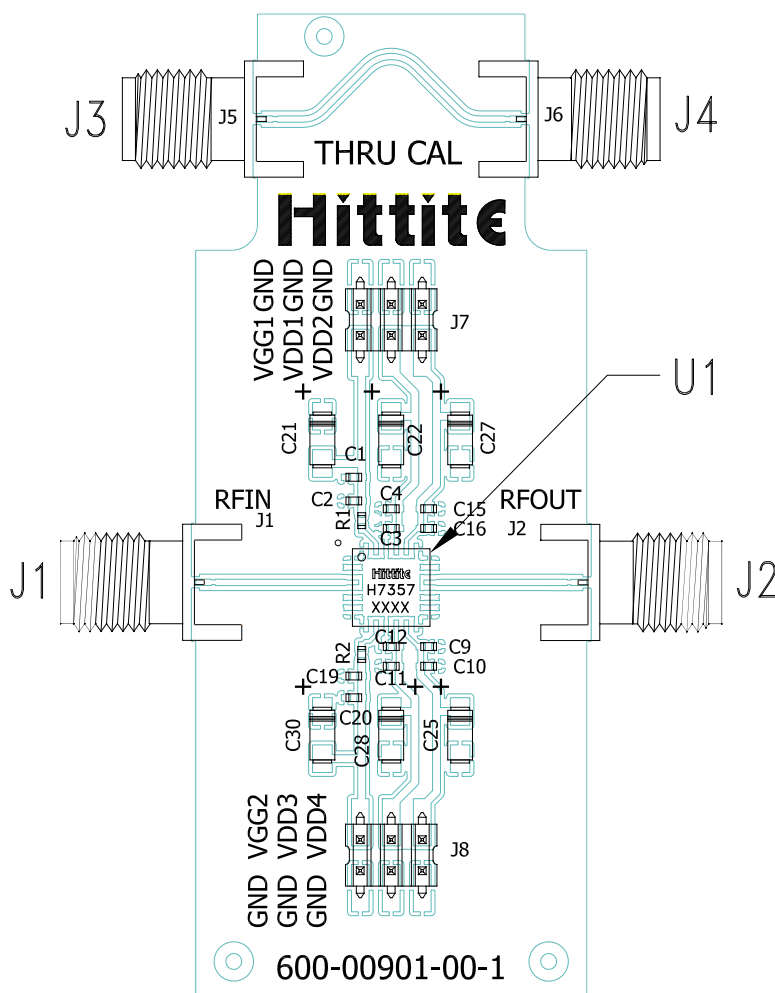
**GaAs pHEMT MMIC 2 WATT  
POWER AMPLIFIER, 5.5 - 8.5 GHz**
**Pin Descriptions**

| Pad Number                                             | Function                  | Description                                                                                                                                                                          | Interface Schematic                                                                   |
|--------------------------------------------------------|---------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|
| 1, 4, 5, 6, 7, 9,<br>12, 13, 14, 17,<br>18, 19, 22, 24 | N/C                       | These pins are not connected internally; however all data shown herein was measured with these pins connected to RF/DC ground externally.                                            |                                                                                       |
| 2, 15                                                  | GND                       | These pins and exposed ground paddle must be connected to RF/DC ground.                                                                                                              |    |
| 3                                                      | RFIN                      | This pin is DC coupled and matched to 50 Ohms.                                                                                                                                       |    |
| 8, 23                                                  | Vgg2, Vgg1                | Gate control for PA. Adjust Vgg to achieve recommended bias current. External bypass capacitors of 100 pF, 10 nF, and 4.7 μF are required. Apply Vgg bias to either pin 8 or pin 23. |    |
| 10, 11, 20, 21                                         | Vdd3, Vdd4, Vdd2,<br>Vdd1 | Drain bias voltage for the amplifier. External bypass capacitors of 100 pF, 10 nF, and 4.7 μF are required.                                                                          |   |
| 16                                                     | RFOUT                     | This pin is DC coupled and matched to 50 Ohms.                                                                                                                                       |  |

**GaAs pHEMT MMIC 2 WATT  
POWER AMPLIFIER, 5.5 - 8.5 GHz**

**Application Circuit**



**GaAs pHEMT MMIC 2 WATT  
POWER AMPLIFIER, 5.5 - 8.5 GHz**
**Evaluation PCB**

**List of Materials for Evaluation PCB EV1HMC7357LP5 <sup>[1]</sup>**

| Item                         | Description                   |
|------------------------------|-------------------------------|
| J1 - J4                      | "K" Connector, SRI            |
| J7, J8                       | DC Pin                        |
| C2, C3, C9, C12, C16, C19    | 100 pF Capacitor, 0402 Pkg.   |
| C1, C4, C10, C11, C15, C20   | 10000 pF Capacitor, 0402 Pkg. |
| C21, C22, C25, C27, C28, C30 | 4.7 uF Capacitor, Case A Pkg. |
| R1, R2                       | 43.2 Ohm Resistor, 0402 Pkg   |
| U1                           | HMC7357LP5GE Amplifier        |
| PCB <sup>[2]</sup>           | 600-00901-00 Eval Board       |

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Analog Devices, upon request.



## HMC7357LP5GE

v01.0918

**GaAs pHEMT MMIC 2 WATT  
POWER AMPLIFIER, 5.5 - 8.5 GHz**

**Notes:**

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